

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA373FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

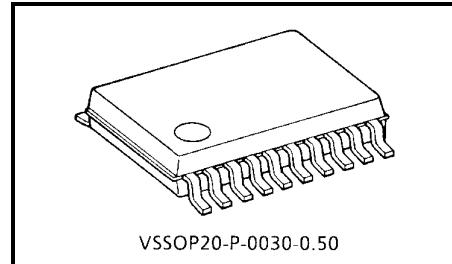
The TC7MA373FK is a high performance CMOS octal D-type latch which is guaranteed to operate from 1.2-V to 3.6-V. Designed for use in 1.5 V, 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

The 8 bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

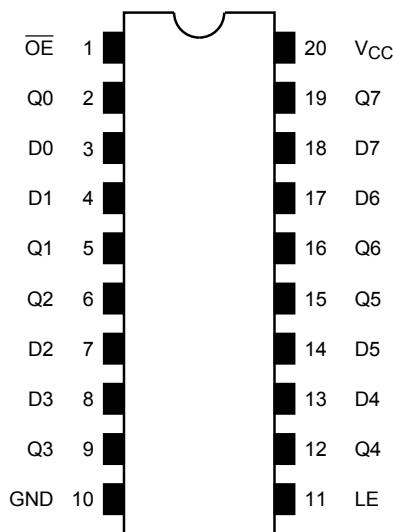
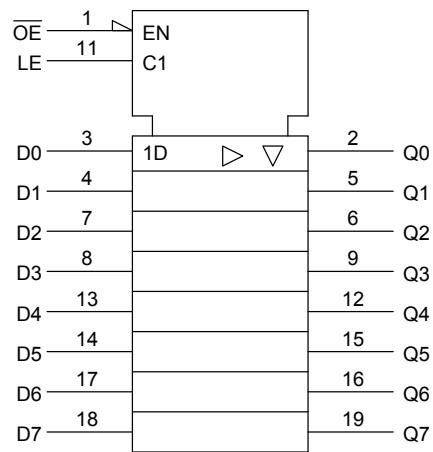
All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

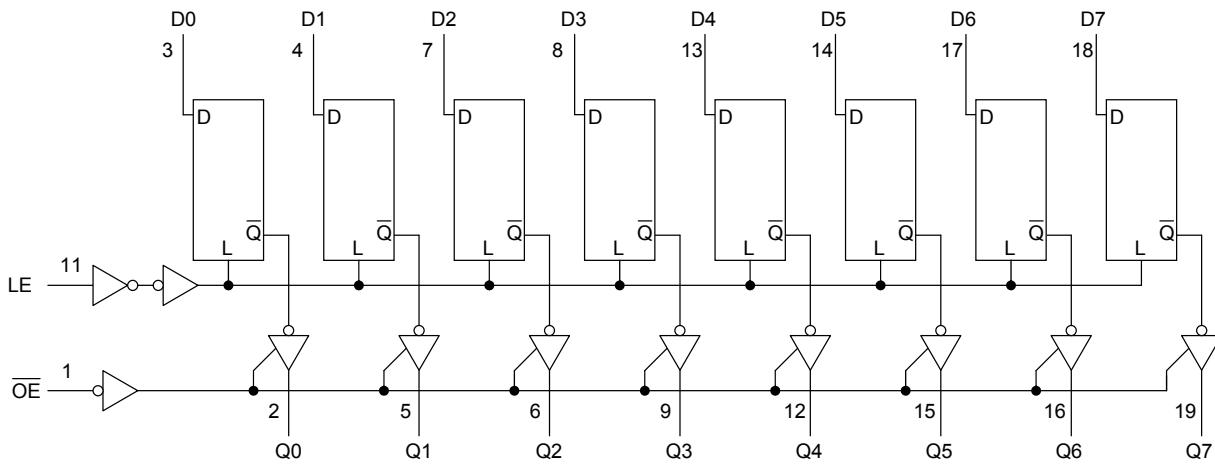
- Low voltage operation: $V_{CC} = 1.2\sim 3.6$ V
- High speed operation: $t_{pd} = 4.2$ ns (max) ($V_{CC} = 3.0\sim 3.6$ V)
 $t_{pd} = 4.7$ ns (max) ($V_{CC} = 2.3\sim 2.7$ V)
 $t_{pd} = 9.4$ ns (max) ($V_{CC} = 1.65\sim 1.95$ V)
 $t_{pd} = 18.8$ ns (max) ($V_{CC} = 1.4\sim 1.6$ V)
 $t_{pd} = 47.0$ ns (max) ($V_{CC} = 1.2$ V)
- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
 $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
 $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.65$ V)
 $I_{OH}/I_{OL} = \pm 2$ mA (min) ($V_{CC} = 1.4$ V)
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200$ V
Human body model $\geq \pm 2000$ V
- Package: VSSOP (US)
- Power down protection is provided on all inputs and outputs.

Pin Assignment (top view)**IEC Logic Level****Truth Table**

Inputs			Outputs
\overline{OE}	LE	D	
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X: Don't care

Z: High impedance

 Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.**System Diagram**

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage	V _{IN}	-0.5~4.6	V
DC output voltage	V _{OUT}	-0.5~4.6 (Note 2)	V
		-0.5~V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Off-state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: V_{OUT} < GND, V_{OUT} > V_{CC}

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.2~3.6	V
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	V _{OUT}	0~3.6 (Note 2)	V
		0~V _{CC} (Note 3)	
Output current	I _{OH} /I _{OL}	±24 (Note 4)	mA
		±18 (Note 5)	
		±6 (Note 6)	
		±2 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either V_{CC} or GND.

Note 2: V_{CC} = 0 V

Note 3: High or low state

Note 4: V_{CC} = 3.0~3.6 V

Note 5: V_{CC} = 2.3~2.7 V

Note 6: V_{CC} = 1.65~1.95 V

Note 7: V_{CC} = 1.4~1.6 V

Note 8: V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level		—	2.7~3.6					
	Low level	V _{IL}	—	2.7~3.6	—	0.8	—		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	—	V	
				I _{OH} = -12 mA	2.7	2.2	—		
				I _{OH} = -18 mA	3.0	2.4	—		
				I _{OH} = -24 mA	3.0	2.2	—		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	—	0.2		
				I _{OL} = 12 mA	2.7	—	0.4		
				I _{OL} = 18 mA	3.0	—	0.4		
				I _{OL} = 24 mA	3.0	—	0.55		
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	—	±5.0	μA	
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.7~3.6	—	±10.0	μA	
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		2.7~3.6	—	20.0	μA		
		V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7~3.6	—	±20.0			
	ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V (per input)		2.7~3.6	—	750			

DC Characteristics (Ta = -40~85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	High level		—	2.3~2.7					
	Low level	V _{IL}	—	2.3~2.7	—	0.7	—		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V	
				I _{OH} = -6 mA	2.3	2.0	—		
				I _{OH} = -12 mA	2.3	1.8	—		
				I _{OH} = -18 mA	2.3	1.7	—		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2		
				I _{OL} = 12 mA	2.3	—	0.4		
				I _{OL} = 18 mA	2.3	—	0.6		
				I _{OL} = 24 mA	2.3~2.7	—	0.8		
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA	
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.3~2.7	—	±10.0	μA	
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		2.3~2.7	—	20.0	μA		
		V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3~2.7	—	±20.0			

DC Characteristics (Ta = -40~85°C, 1.65 V ≤ V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		1.65~2.3	0.65 × V _{CC}	—	V
	Low level	V _{IL}	—		1.65~2.3	—	0.2 × V _{CC}	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA I _{OH} = -6 mA	1.65~2.3 1.65	V _{CC} - 0.2 1.25	—	V
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA I _{OL} = 6 mA	1.65~2.3 1.65	—	0.2 0.3	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		1.65~2.3	—	±5.0	μA
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		1.65~2.3	—	±10.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.65~2.3 1.65~2.3	—	20.0 ±20.0	μA

DC Characteristics (Ta = -40~85°C, 1.4 V ≤ V_{CC} < 1.65 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		1.4~1.65	0.65 × V _{CC}	—	V
	Low level	V _{IL}	—		1.4~1.65	—	0.05 × V _{CC}	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA I _{OH} = -2 mA	1.4~1.65 1.4	V _{CC} - 0.2 1.05	—	V
	Low level	V _{OL}		I _{OL} = 100 μA I _{OL} = 2 mA	1.4~1.65 1.4	—	0.05 0.35	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		1.4~1.65	—	±5.0	μA
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		1.4~1.65	—	±10.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.4~1.65 1.4~1.65	—	20.0 ±20.0	μA

DC Characteristics ($T_a = -40\text{~}85^\circ\text{C}$, $1.2 \text{ V} \leq V_{CC} < 1.4 \text{ V}$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	High level	V_{IH}	—			1.2~1.4	$0.8 \times V_{CC}$	—	
	Low level	V_{IL}	—			1.2~1.4	—	$0.05 \times V_{CC}$	
Output voltage	High level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	1.2	$V_{CC} - 0.1$	—	V	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	1.2	—	0.05	V	
Input leakage current	I_{IN}	$V_{IN} = 0\text{~}3.6 \text{ V}$		1.2	—	± 5.0	μA		
3-state output off-state current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0\text{~}3.6 \text{ V}$		1.2	—	± 10.0	μA		
Power off leakage current	I_{OFF}	$V_{IN}, V_{OUT} = 0\text{~}3.6 \text{ V}$		0	—	10.0	μA		
Quiescent supply current	I_{CC}	$V_{IN} = V_{CC}$ or GND		1.2	—	20.0	μA		
		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.2	—	± 20.0			

AC Characteristics (Ta = -40~85°C, Input: t_r = t_f = 2.0 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Propagation delay time (D-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	1.5	47.0
				1.5 ± 0.1	1.0	18.8
				1.8 ± 0.15	1.5	9.4
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	0.8	4.7
				3.3 ± 0.3	0.6	4.2
						ns
Propagation delay time (LE-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	1.5	49.0
				1.5 ± 0.1	1.0	19.6
				1.8 ± 0.15	1.5	9.8
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	0.8	4.9
				3.3 ± 0.3	0.6	4.2
						ns
3-state output enable time	t _{pZL} t _{pZH}	Figure 1, Figure 3	C _L = 15 pF, R _L = 2 kΩ	1.2	1.5	49.0
				1.5 ± 0.1	1.0	19.6
				1.8 ± 0.15	1.5	9.8
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	0.8	5.5
				3.3 ± 0.3	0.6	4.5
						ns
3-state output disable time	t _{pLZ} t _{pHZ}	Figure 1, Figure 3	C _L = 15 pF, R _L = 2 kΩ	1.2	1.5	32.5
				1.5 ± 0.1	1.0	13.0
				1.8 ± 0.15	1.5	6.5
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	0.8	3.6
				3.3 ± 0.3	0.6	3.3
						ns
Minimum pulse width (LE)	t _w (H)	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	24	—
				1.5 ± 0.1	8.0	—
				1.8 ± 0.15	4.0	—
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	1.5	—
				3.3 ± 0.3	1.5	—
						ns
Minimum set-up time	t _s	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	20	—
				1.5 ± 0.1	7.5	—
				1.8 ± 0.15	2.5	—
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	1.5	—
				3.3 ± 0.3	1.5	—
						ns
Minimum hold time	t _h	Figure 1, Figure 2	C _L = 15 pF, R _L = 2 kΩ	1.2	8.0	—
				1.5 ± 0.1	3.0	—
				1.8 ± 0.15	1.0	—
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	1.0	—
				3.3 ± 0.3	1.0	—
						ns
Output to output skew	t _{osLH} t _{osHL}	(Note)	C _L = 15 pF, R _L = 2 kΩ	1.2	—	1.5
				1.5 ± 0.1	—	1.5
				1.8 ± 0.15	—	0.5
			C _L = 30 pF, R _L = 500 Ω	2.5 ± 0.2	—	0.5
				3.3 ± 0.3	—	0.5
						ns

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design. (t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLM} - t_{pHLn}|)

Dynamic Switching Characteristics (Ta = 25°C, Input: t_r = t_f = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{O LP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	0.8	
Quiet output minimum dynamic V _{OL}	V _{O LV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	-0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	-0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	-0.8	
Quiet output minimum dynamic V _{OH}	V _{O HV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	1.5	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	1.9	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	2.2	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

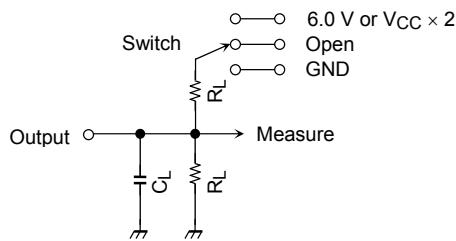
Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Output capacitance	C _O	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

AC Test Circuit

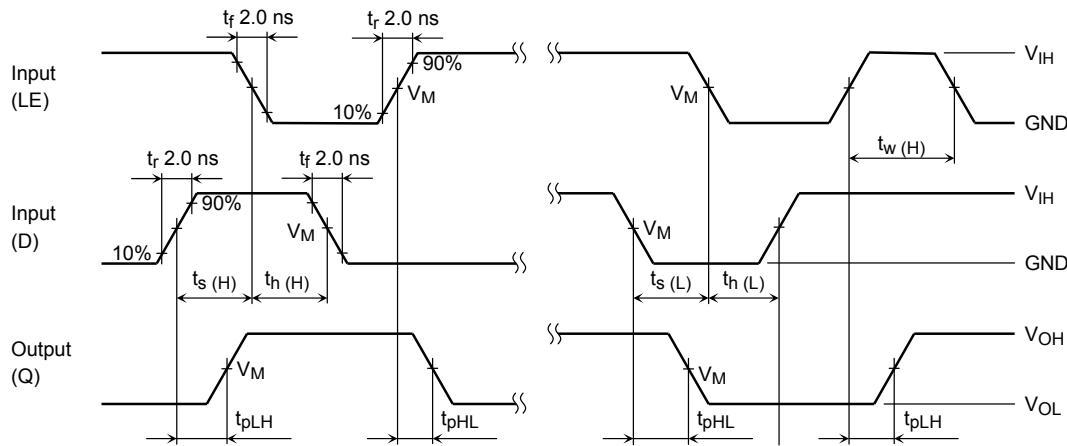


Parameter	Switch
t_{PLH}, t_{PHL}	Open
t_{PLZ}, t_{PZL}	6.0 V $V_{CC} \times 2$ @ $V_{CC} = 3.3 \pm 0.3$ V @ $V_{CC} = 2.5 \pm 0.2$ V @ $V_{CC} = 1.8 \pm 0.15$ V @ $V_{CC} = 1.5 \pm 0.1$ V @ $V_{CC} = 1.2$ V
t_{PHZ}, t_{PZH}	GND

Symbol	V_{CC}	
	3.3 ± 0.3 V 2.5 ± 0.2 V 1.8 ± 0.15 V	1.5 ± 0.1 V 1.2 V
R_L	500Ω	2kΩ
C_L	30pF	15pF

Figure 1

AC Waveform

Figure 2 $t_{PLH}, t_{PHL}, t_w, t_s, t_h$

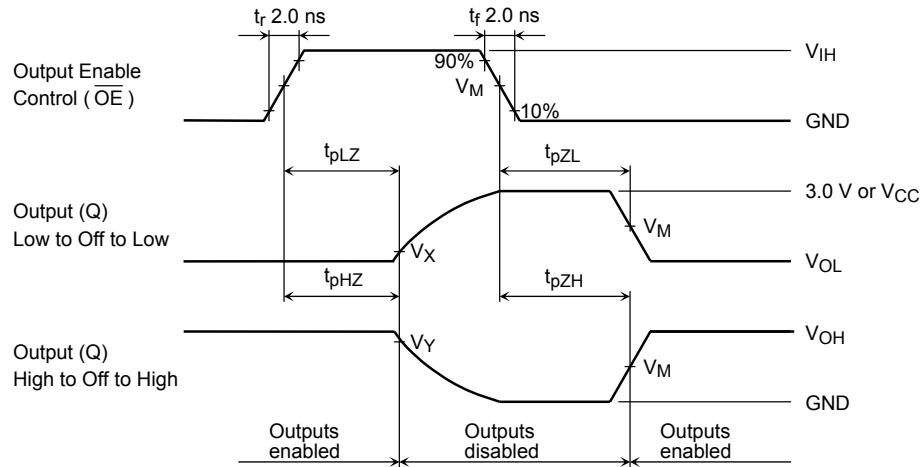


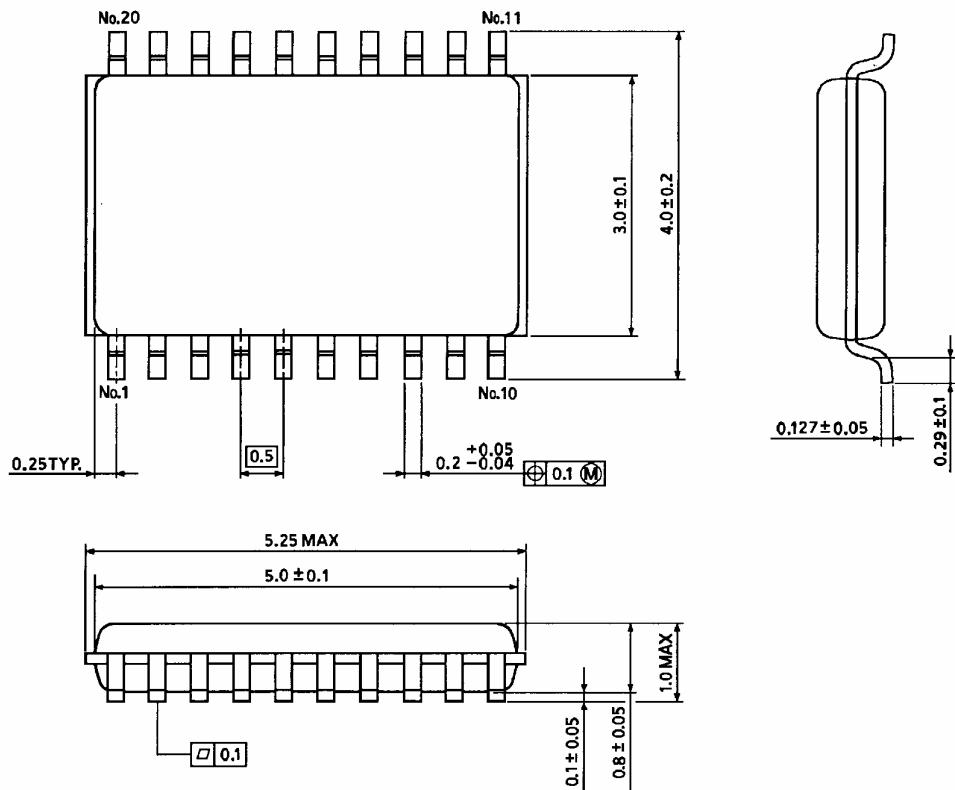
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}				
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 ± 0.15 V	1.5 ± 0.1 V	1.2 V
V_{IH}	2.7 V	V_{CC}	V_{CC}	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.1$ V	$V_{OL} + 0.1$ V
V_Y	$V_{OH} - 0.3$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.1$ V	$V_{OH} - 0.1$ V

Package Dimensions

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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